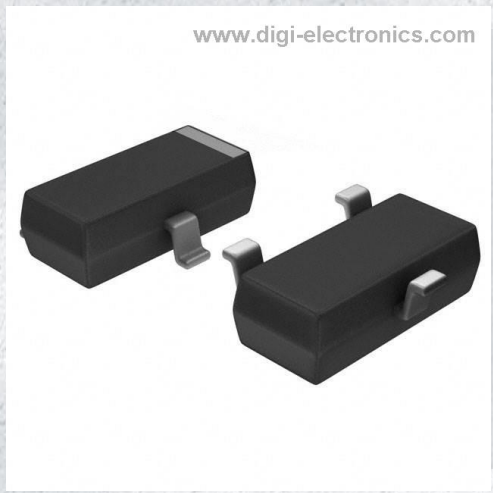
SMBTA 42 E6433 Datasheet



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DiGi Electronics Part Number	SMBTA 42 E6433-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	SMBTA 42 E6433
Description	TRANS NPN 300V 0.5A SOT23
Detailed Description	Bipolar (BJT) Transistor NPN 300 V 500 mA 70MHz 360 mW Surface Mount PG-SOT23

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

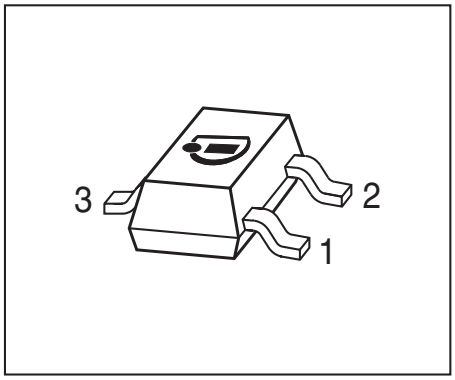
Manufacturer Product Number:	Manufacturer:
SMBTA 42 E6433	Infineon Technologies
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
300 V	500mV @ 2mA, 20mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	40 @ 30mA, 10V
Power - Max:	Frequency - Transition:
360 mW	70MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	PG-SOT23
Base Product Number:	
SMBTA 42	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095

SMBTA42/MMBTA42

NPN Silicon High-Voltage Transistors



- Low collector-emitter saturation voltage
- Complementary types:
  SMBTA92 / MMBTA92(PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

Type	Marking	Pin Configuration			Package
SMBTA42/MMBTA42	s1D	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	300	V
Collector-base voltage	V_{CBO}	300	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	500	mA
Base current	I_B	100	
Total power dissipation- $T_S \leq 74$ °C	P_{tot}	360	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 210	K/W

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

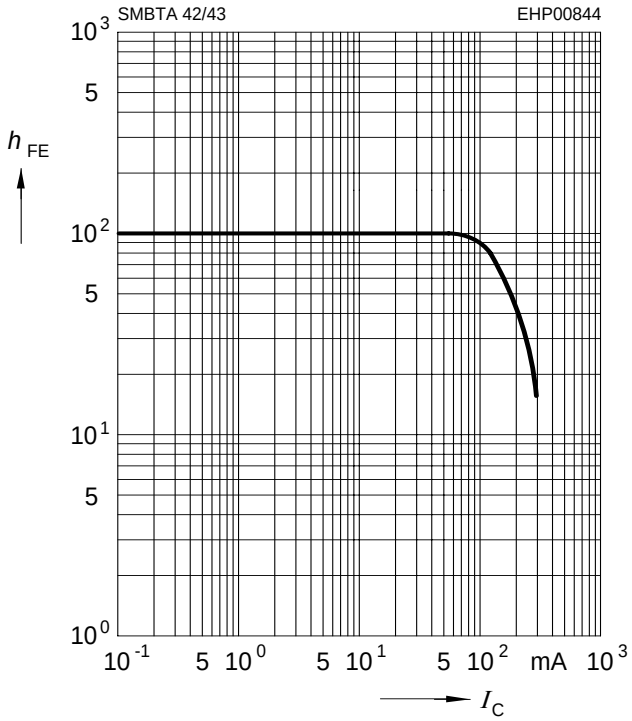
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	300	-	-	V
Collector-base breakdown voltage I_C = 100 µA, I_E = 0	$V_{(BR)CBO}$	300	-	-	
Emitter-base breakdown voltage I_E = 100 µA, I_C = 0	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current V_{CB} = 200 V, I_E = 0 V_{CB} = 200 V, I_E = 0 , T_A = 150 °C	I_{CBO}	 - -	 - -	 0.1 20	µA
Emitter-base cutoff current V_{EB} = 5 V, I_C = 0	I_{EBO}	-	-	100	nA
DC current gain[1)] I_C = 1 mA, V_{CE} = 10 V I_C = 10 mA, V_{CE} = 10 V I_C = 30 mA, V_{CE} = 10 V	h_{FE}	 25 40 40	 - - -	 - - -	-
Collector-emitter saturation voltage[1)] I_C = 20 mA, I_B = 2 mA	V_{CEsat}	-	-	0.5	V
Base emitter saturation voltage[1)] I_C = 20 mA, I_B = 2 mA	V_{BEsat}	-	-	0.9	
AC Characteristics					
Transition frequency I_C = 10 MHz, V_{CE} = 20 V, f = 100 MHz	f_T	50	70	-	MHz
Collector-base capacitance V_{CB} = 20 V, f = 1 MHz	C_{cb}	-	-	3	pF

[1]Pulse test: t < 300µs; D < 2%

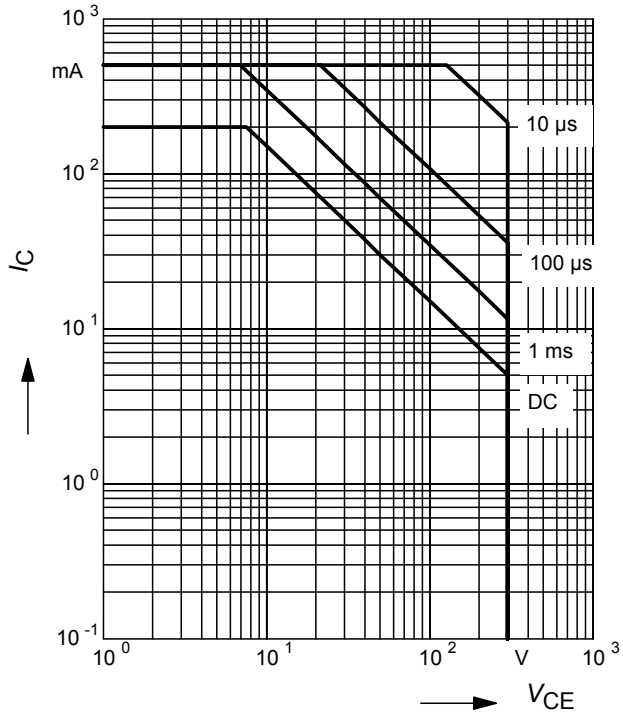
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 10 V



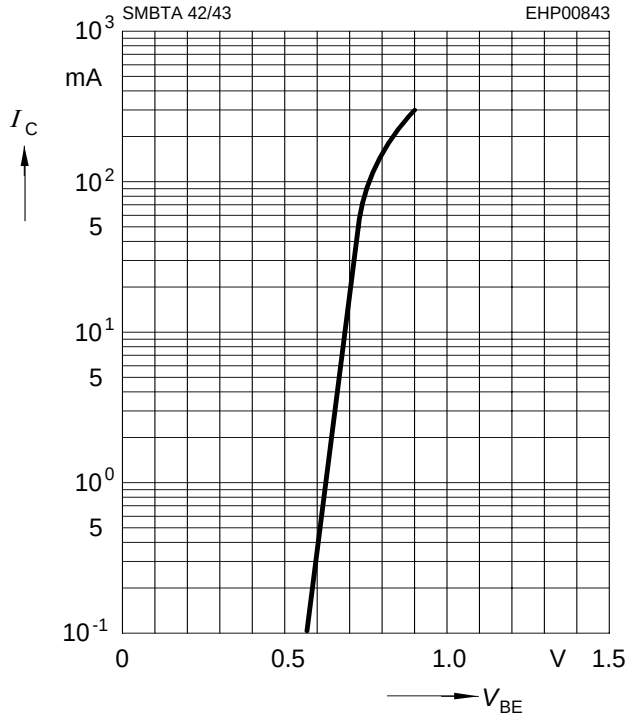
Operating range $I_C = f(V_{CEO})$

T_A = 25°C, D = 0



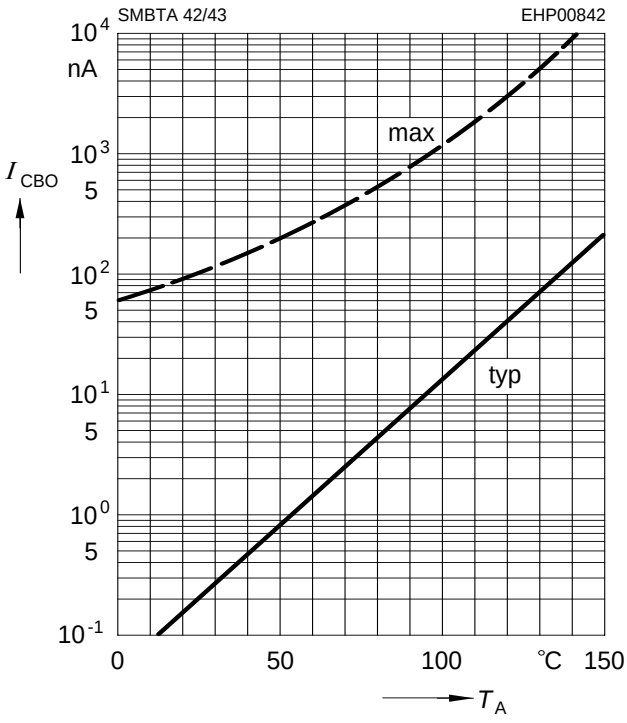
Collector current $I_C = f(V_{BE})$

V_{CE} = 10V



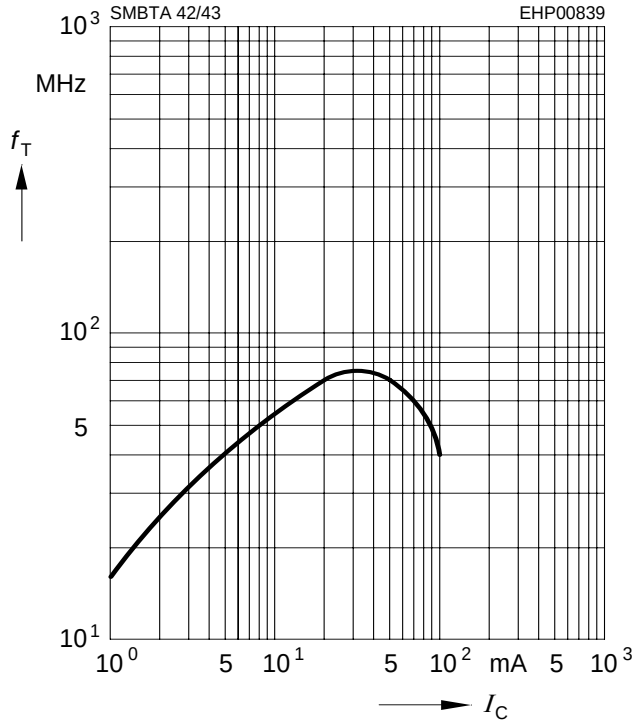
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CBO} = 160 V



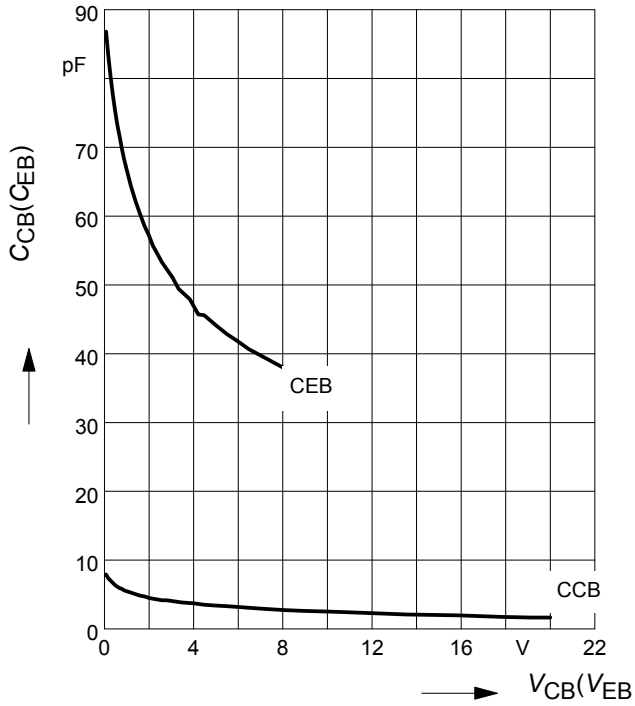
Transition frequency $f_T = f(I_C)$

V_{CE} = 10 V, f = 100 MHz

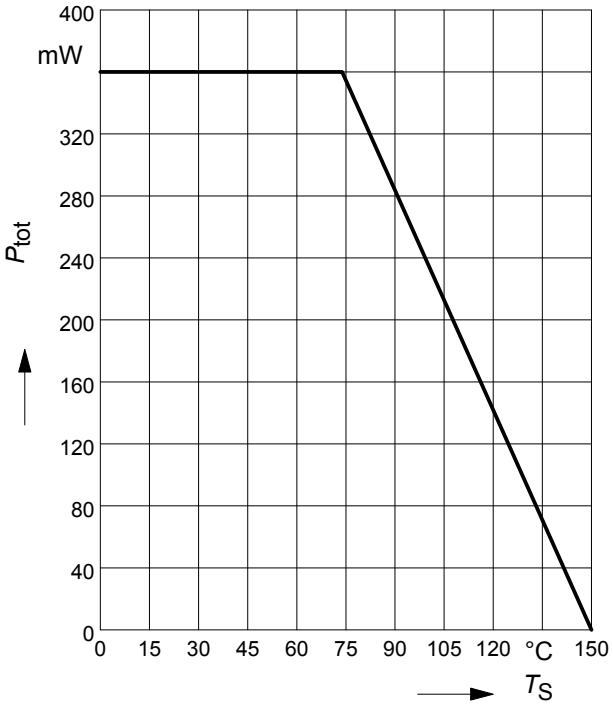


Collector-base capacitance $C_{cb} = f(V_{CB})$

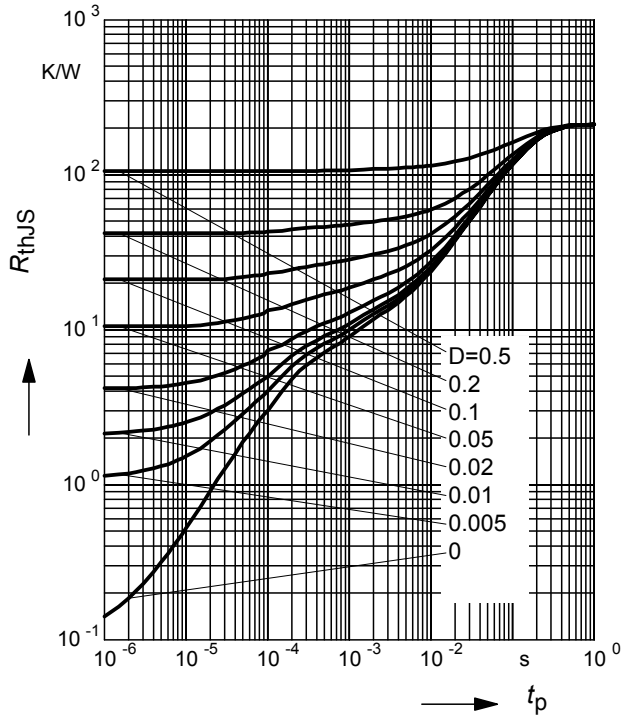
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

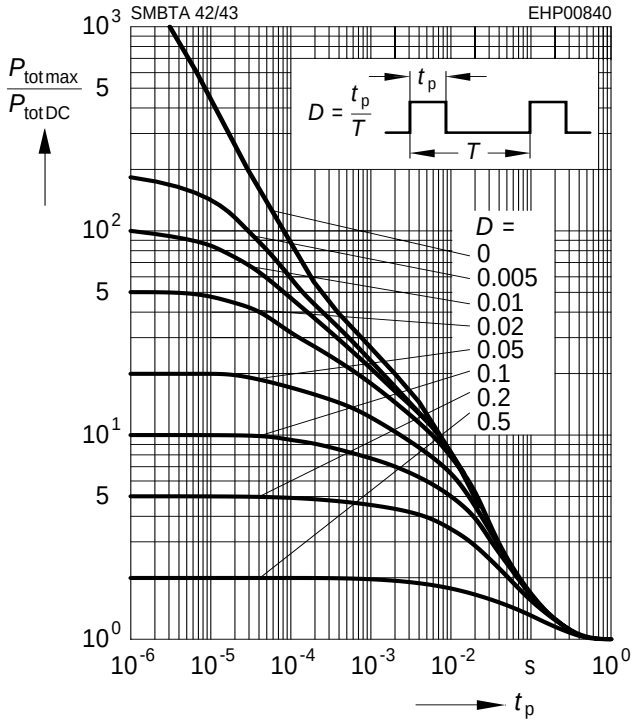


Permissible Pulse Load $R_{thJS} = f(t_p)$

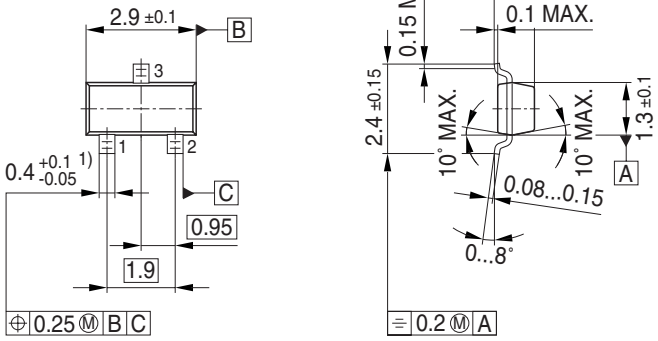


Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

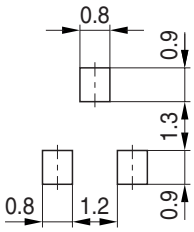


Package Outline

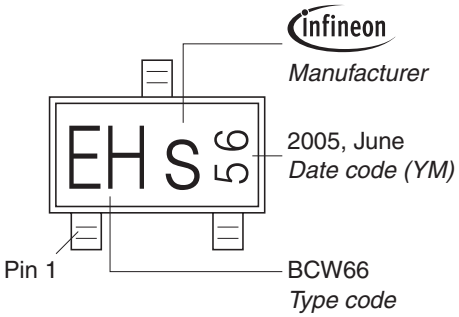


1) Lead width can be 0.6 max. in dambar area

Foot Print

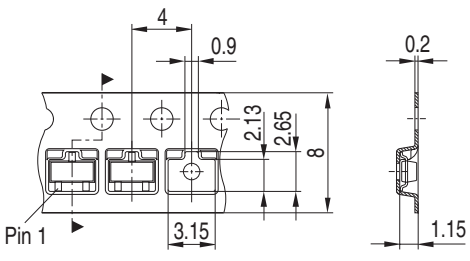


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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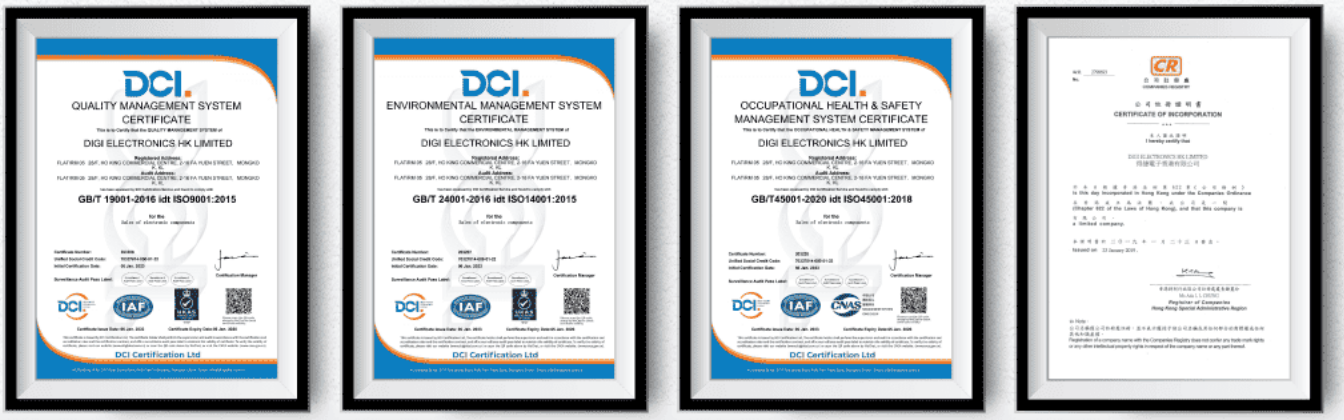

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